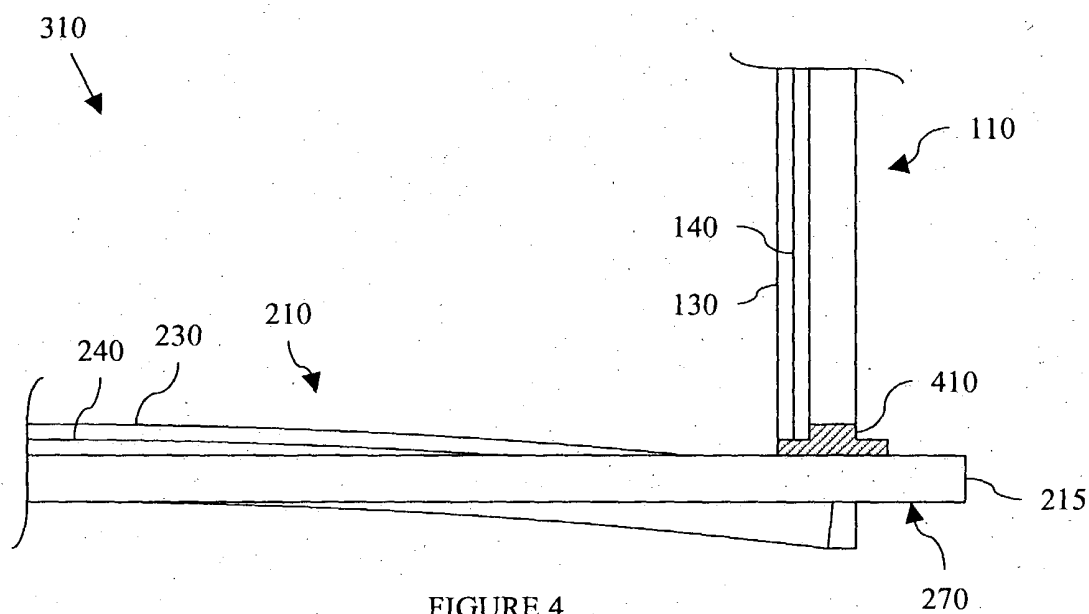
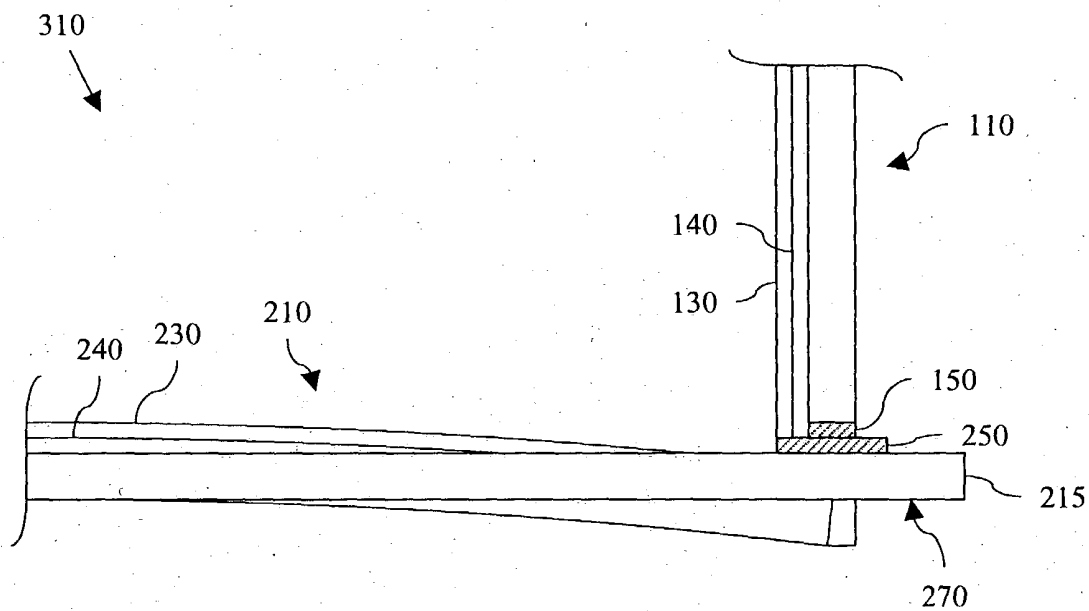


FIG. 1 is a cross-sectional view of a multi-layered structure. The structure consists of alternating layers 130 and 140. A central core 115 is flanked by two vertical structures 120. Each vertical structure 120 has a central core 125 and is surrounded by a layer 135. The entire structure is supported by a base 150. Arrows 117 point to the interfaces between the layers 130 and 140.

FIGURE 1

This diagram shows a cross-sectional view of a semiconductor device. It features a central gap (220) between two main structures. Each structure consists of a central core (215) flanked by side regions (219). The top surface is covered by a layer (217) with a central opening (235). The bottom surface is divided into regions (230, 240, 230) by vertical lines (250). Arrows indicate the direction of light or signal flow.

FIGURE 2



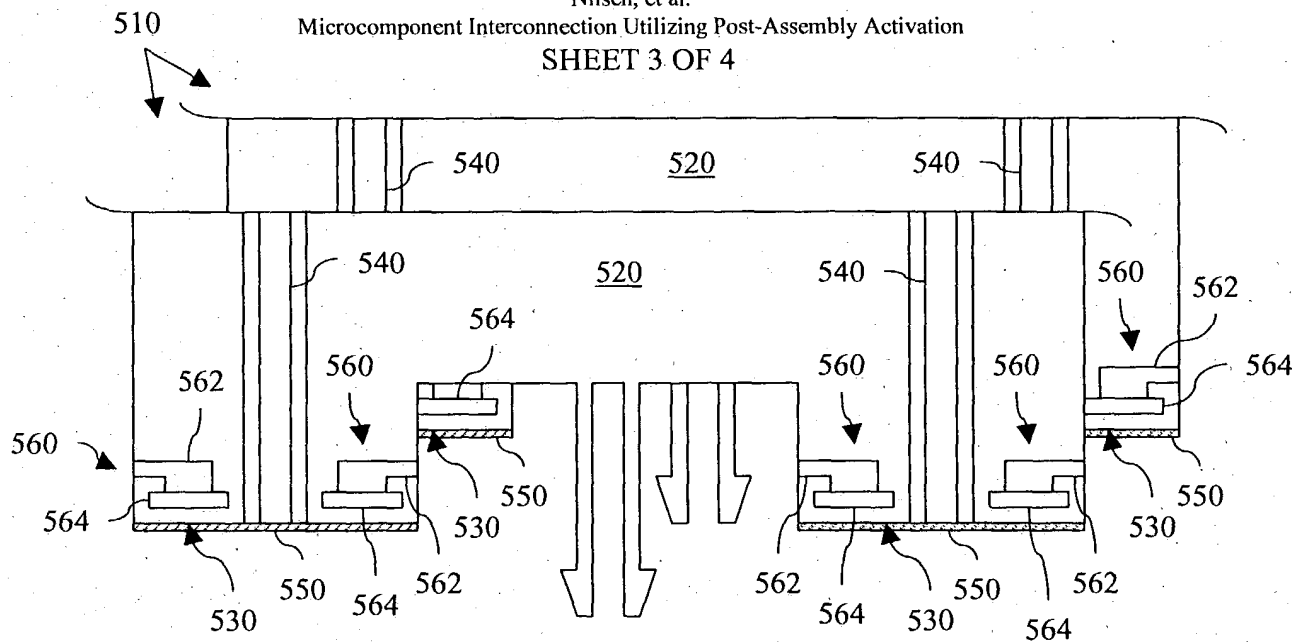


FIGURE 5

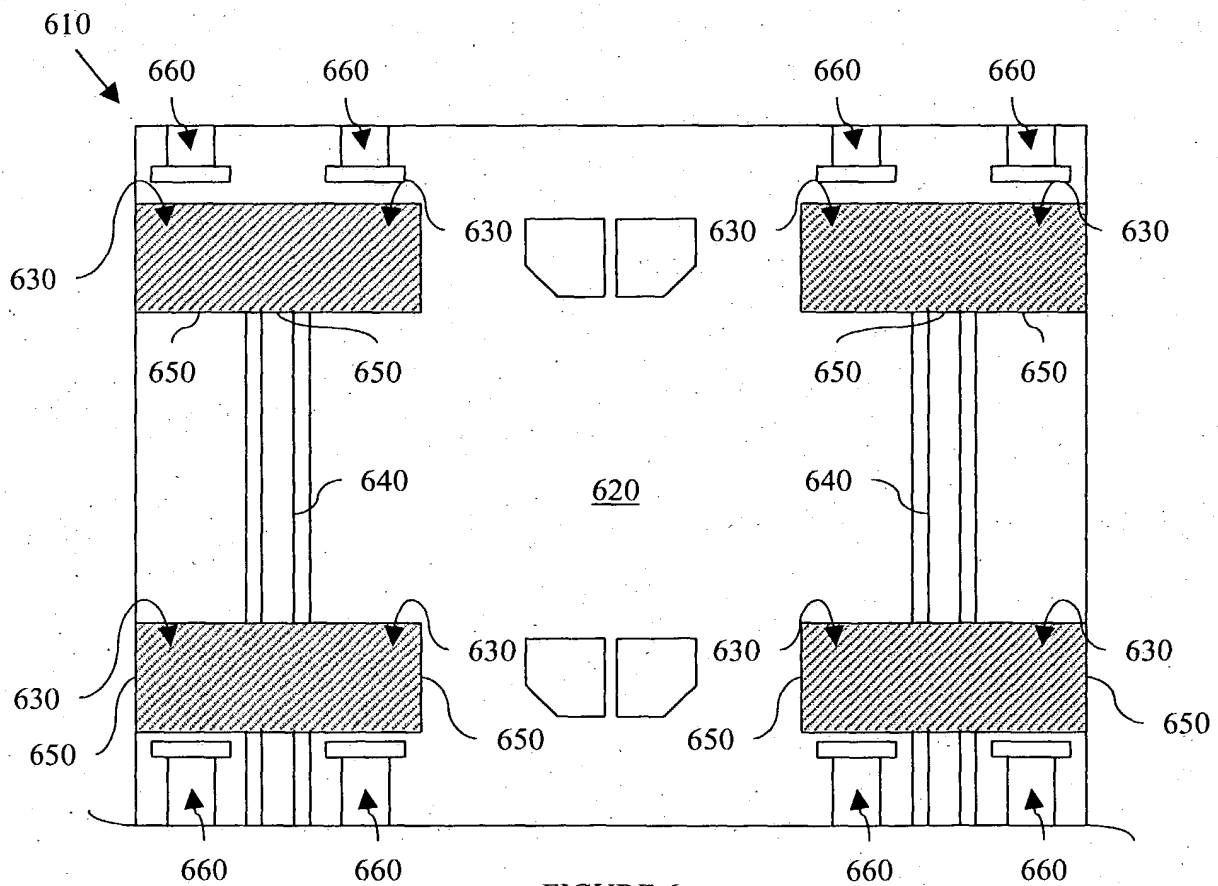


FIGURE 6

SHEET 4 OF 4

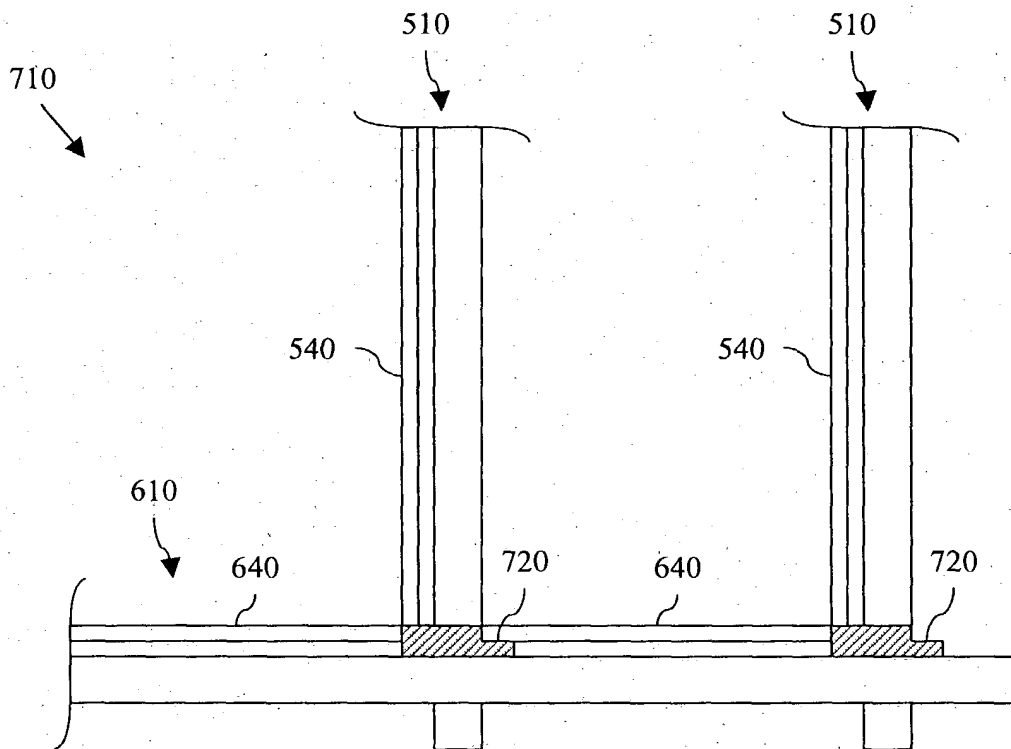


FIGURE 7